

Docket No.: 21302/0204309-US0

(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

---

In re Patent Application of:  
Euijoon Yoon *et al.*

Application No.: 10/596,126

Confirmation No.: 2554

Filed: May 31, 2006

Art Unit: 2813

For: GROWTH METHOD OF NITRIDE  
SEMICONDUCTOR LAYER AND LIGHT  
EMITTING DEVICE USING THE GROWTH  
METHOD

---

Examiner: Crawford, LaTanya N.

**RESPONSE TO NON-FINAL OFFICE ACTION**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

March 10, 2010

**INTRODUCTORY COMMENTS**

Dear Sir:

In response to the Non-Final Office Action dated December 16, 2009, please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 7 of this paper.